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JAN 18 2005

TRANSMITTAL OF FORMAL DRAWINGS

Docket No.
YOR920030102US2 (16476Z)

In Re Application Of: **Stephen W. Bedell, et al.**

Application No.	Filing Date	Confirmation No.	Examiner	Customer No.	Group Art Unit
10/696,601	October 29, 2003	6851	Stephen J. Stein	23389	1775

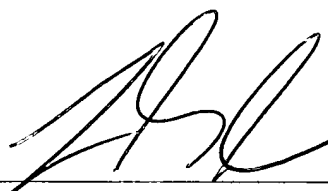
Invention: **FORMATION OF SILICON-GERMANIUM-ON-INSULATOR (SGOI) BY AN INTEGRAL HIGH TEMPERATURE SIMOX-Ge INTERDIFFUSION ANNEAL**

Address to:
Commissioner for Patents
P.O. Box 1450
Alexandria, VA 22313-1450

Transmitted herewith are:

7 sheets of formal drawing(s) for this application.

☒ Each sheet of drawing indicates the identifying indicia suggested in 37 CFR Section 1.84(c).



Signature

**Leslie S. Szivos, Ph. D.
Registration No. 39,394**

Dated: **January 7, 2005**

I certify that this document and attached formal drawings are being deposited on **01/07/05** with the U.S. Postal Service as first class mail under 37 C.F.R. 1.8 and addressed to the Commissioner for Patents, P.O. Box 1450, Alexandria, VA 22313-1450.

Signature of Person Mailing Correspondence

Leslie S. Szivos, Ph.D. Reg. No. 39,394

Typed or Printed Name of Person Mailing Correspondence